

U.S.S.N. 10/827,065

In the Specification

Please amend the specification on page 10, line 5, as follows:

The present invention discloses a novel hydrogenated oxidized silicon carbon material (SiCOH) comprising Si, C, O and H in a non-polymeric covalently bonded network which is thermally stable to at least 350°C and having a dielectric constant of not more than 3.6. The present invention further discloses a method for fabricating SiCOH films in a parallel plate plasma enhanced chemical vapor deposition chamber. A precursor gas containing Si, O, C and H and optionally containing molecules which have a ring structure can be used for forming the SiCOH film. The SiCOH low dielectric constant film can further be heat treated at a temperature not less than 300°C for at least 0.5 hour to improve its thermal stability.